

# 4V Drive Nch MOSFET

## RSD050N10

### ●Structure

Silicon N-channel MOSFET

### ●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 3) Parallel use is easy.

### ●Applications

Switching

### ●Packaging specifications

|      |                              |      |
|------|------------------------------|------|
| Type | Package                      | CPT3 |
|      | Code                         | TL   |
|      | Basic ordering unit (pieces) | 2500 |

### ●Absolute maximum ratings (T<sub>a</sub>=25°C)

| Parameter                      |            | Symbol             | Limits      | Unit |
|--------------------------------|------------|--------------------|-------------|------|
| Drain-source voltage           |            | V <sub>DSS</sub>   | 100         | V    |
| Gate-source voltage            |            | V <sub>GSS</sub>   | ±20         | V    |
| Drain current                  | Continuous | I <sub>D</sub>     | ±5.0        | A    |
|                                | Pulsed     | I <sub>DP</sub> *1 | ±20         | A    |
| Source current<br>(Body Diode) | Continuous | I <sub>S</sub>     | 5.0         | A    |
|                                | Pulsed     | I <sub>SP</sub> *1 | 20          | A    |
| Power dissipation              |            | P <sub>D</sub> *2  | 15          | W    |
| Channel temperature            |            | T <sub>ch</sub>    | 150         | °C   |
| Range of storage temperature   |            | T <sub>stg</sub>   | -55 to +150 | °C   |

\*1 Pw ≤ 10μs, Duty cycle ≤ 1%

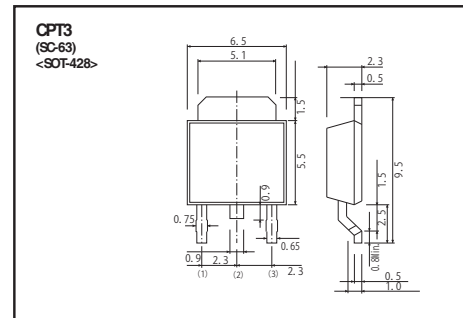
\*2 T<sub>c</sub>=25°C

### ●Thermal resistance

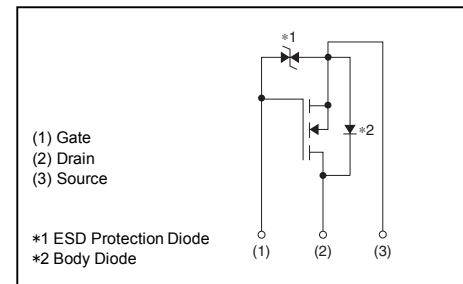
| Parameter       | Symbol                  | Limits | Unit   |
|-----------------|-------------------------|--------|--------|
| Channel to Case | R <sub>th(ch-c)</sub> * | 8.33   | °C / W |

\* T<sub>c</sub>=25°C

### ●Dimensions (Unit : mm)



### ●Inner circuit



**●Electrical characteristics (T<sub>a</sub>=25°C)**

| Parameter                               | Symbol                | Min. | Typ. | Max. | Unit | Conditions                                  |
|---|-----------------------|------|------|------|------|---|
| Gate-source leakage                     | I <sub>GSS</sub>      | -    | -    | ±10  | μA   | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub>  | 100  | -    | -    | V    | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V    |
| Zero gate voltage drain current         | I <sub>DSS</sub>      | -    | -    | 10   | μA   | V <sub>DS</sub> =100V, V <sub>GS</sub> =0V  |
| Gate threshold voltage                  | V <sub>GS(th)</sub>   | 1.0  | -    | 2.5  | V    | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA   |
| Static drain-source on-state resistance | R <sub>DS(on)</sub> * | -    | 135  | 190  | mΩ   | I <sub>D</sub> =5.0A, V <sub>GS</sub> =10V  |
|   |                       | -    | 142  | 200  |      | I <sub>D</sub> =5.0A, V <sub>GS</sub> =4.5V |
|   |                       | -    | 145  | 205  |      | I <sub>D</sub> =5.0A, V <sub>GS</sub> =4.0V |
| Forward transfer admittance             | Y <sub>fs</sub>  *    | 2.5  | -    | -    | S    | I <sub>D</sub> =5.0A, V <sub>DS</sub> =10V  |
| Input capacitance                       | C <sub>ISS</sub>      | -    | 530  | -    | pF   | V <sub>DS</sub> =25V                        |
| Output capacitance                      | C <sub>OSS</sub>      | -    | 50   | -    | pF   | V <sub>GS</sub> =0V                         |
| Reverse transfer capacitance            | C <sub>RSS</sub>      | -    | 30   | -    | pF   | f=1MHz                                      |
| Turn-on delay time                      | t <sub>d(on)</sub> *  | -    | 10   | -    | ns   | I <sub>D</sub> =2.5A, V <sub>DD</sub> ≒ 50V |
| Rise time                               | t <sub>r</sub> *      | -    | 15   | -    | ns   | V <sub>GS</sub> =10V                        |
| Turn-off delay time                     | t <sub>d(off)</sub> * | -    | 45   | -    | ns   | R <sub>L</sub> =20Ω                         |
| Fall time                               | t <sub>f</sub> *      | -    | 15   | -    | ns   | R <sub>G</sub> =10Ω                         |
| Total gate charge                       | Q <sub>g</sub> *      | -    | 14   | -    | nC   | V <sub>DD</sub> ≒ 50V                       |
| Gate-source charge                      | Q <sub>gs</sub> *     | -    | 1.7  | -    | nC   | I <sub>D</sub> =5.0A,                       |
| Gate-drain charge                       | Q <sub>gd</sub> *     | -    | 3.0  | -    | nC   | V <sub>GS</sub> =10V                        |

\*Pulsed

**●Body diode characteristics (Source-Drain) (T<sub>a</sub>=25°C)**

| Parameter       | Symbol            | Min. | Typ. | Max. | Unit | Conditions                                |
|-----------------|-------------------|------|------|------|------|---|
| Forward Voltage | V <sub>SD</sub> * | -    | -    | 1.2  | V    | I <sub>s</sub> =5.0A, V <sub>GS</sub> =0V |

\*Pulsed

●Electrical characteristic curves (T<sub>a</sub>=25°C)

Fig.1 Typical Output Characteristics ( I )

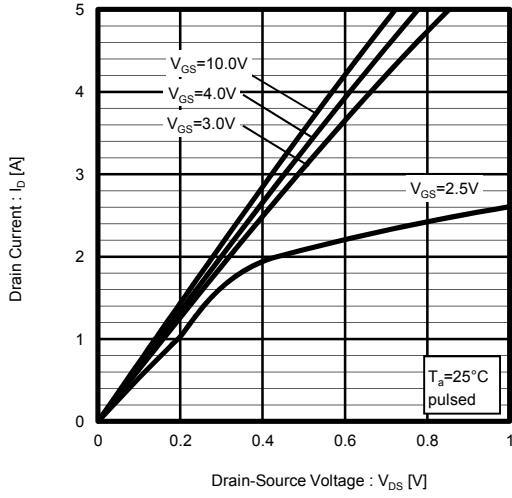


Fig.2 Typical Output Characteristics ( II )

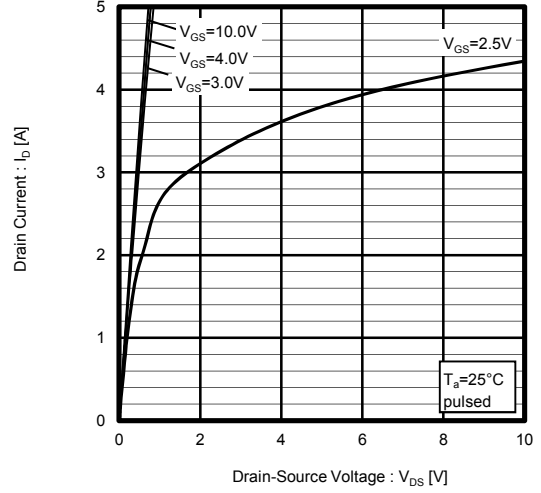


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

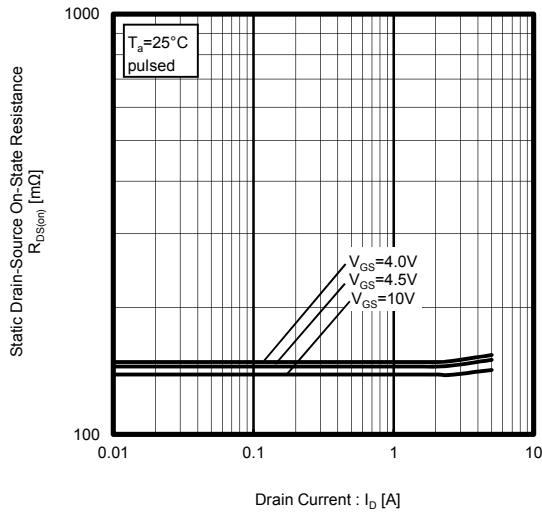


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

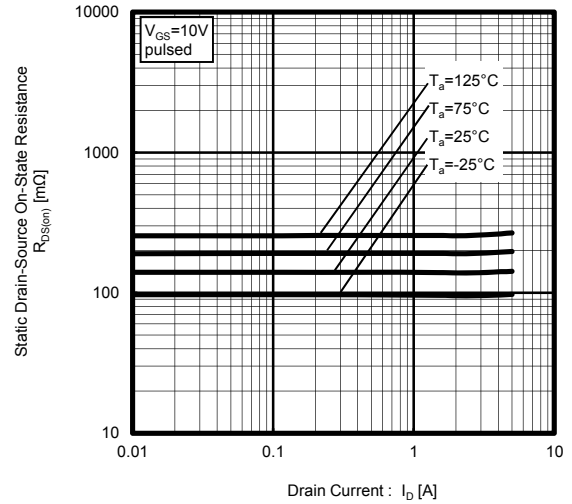


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

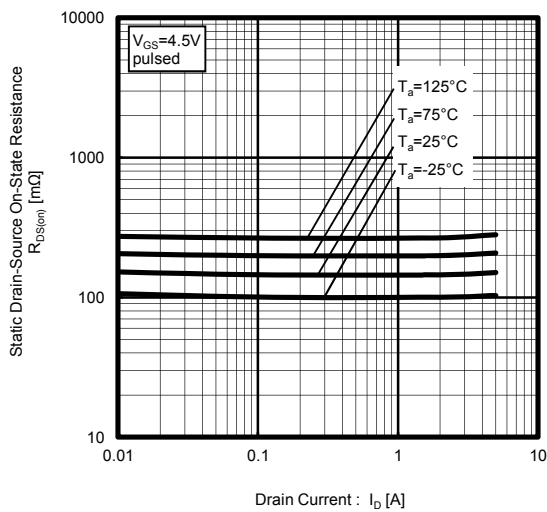


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

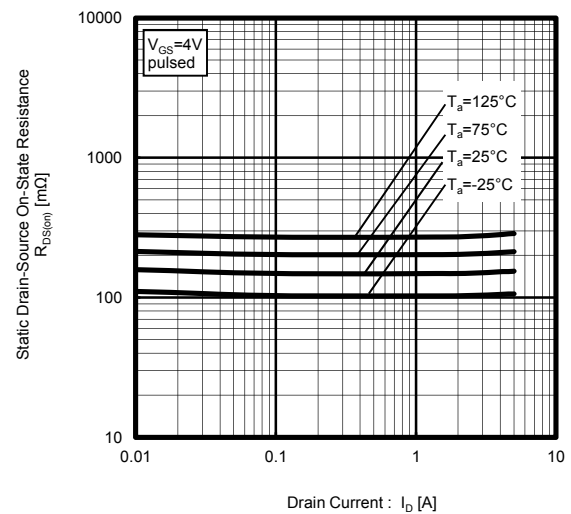


Fig.7 Forward Transfer Admittance vs. Drain Current

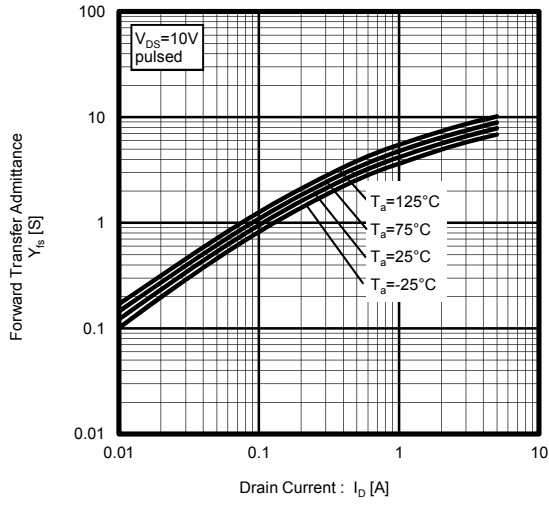


Fig.8 Typical Transfer Characteristics

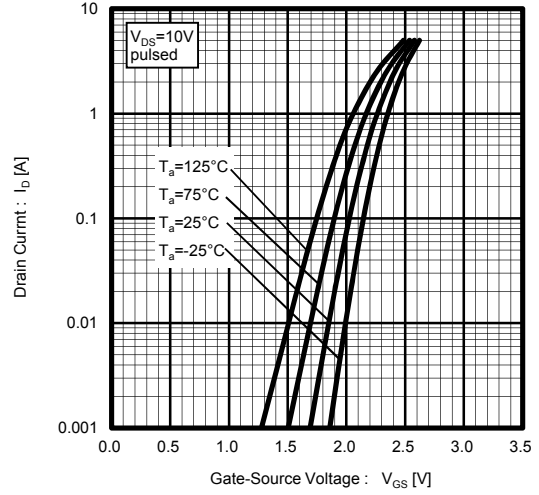


Fig.9 Source Current vs. Source-Drain Voltage

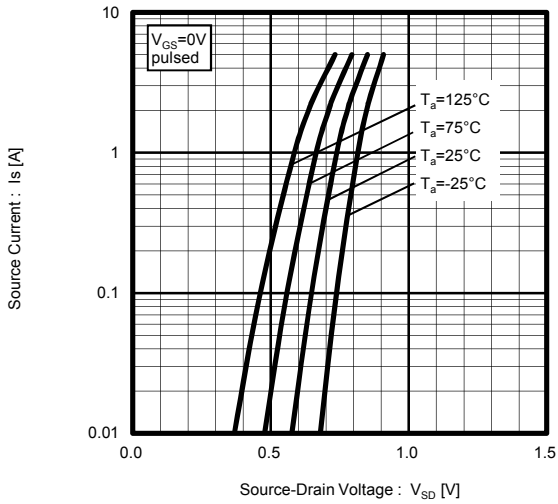


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

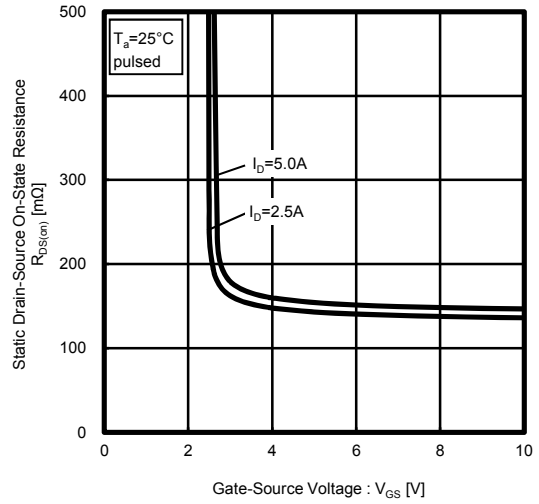


Fig.11 Switching Characteristics

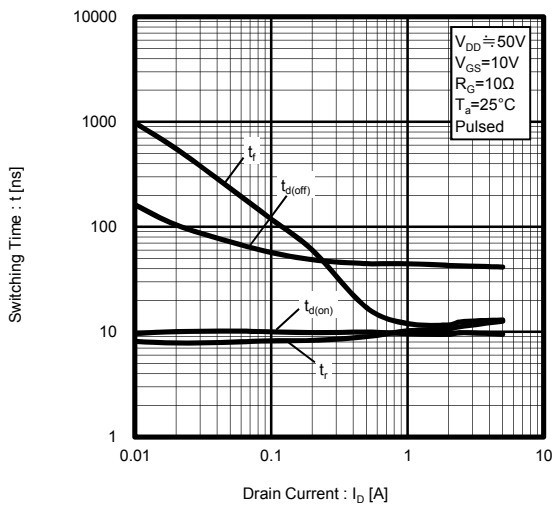


Fig.12 Dynamic Input Characteristics

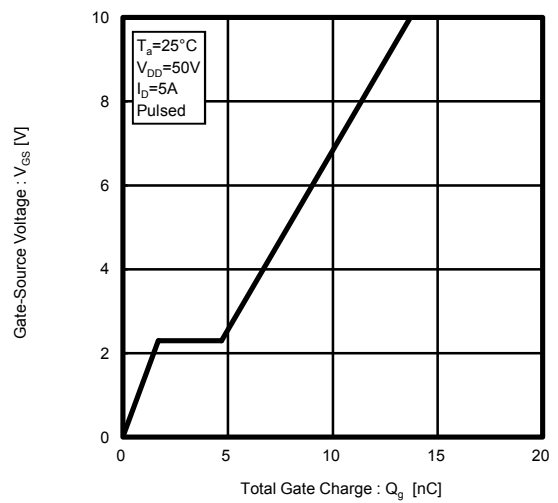


Fig.13 Typical Capacitance vs. Drain-Source Voltage

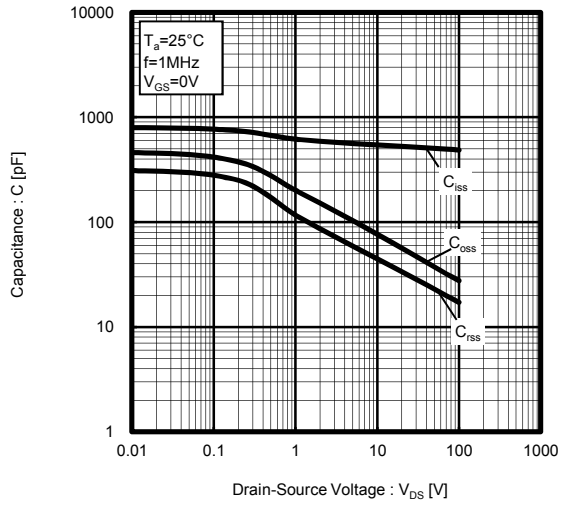


Fig.14 Maximum Safe Operating Area

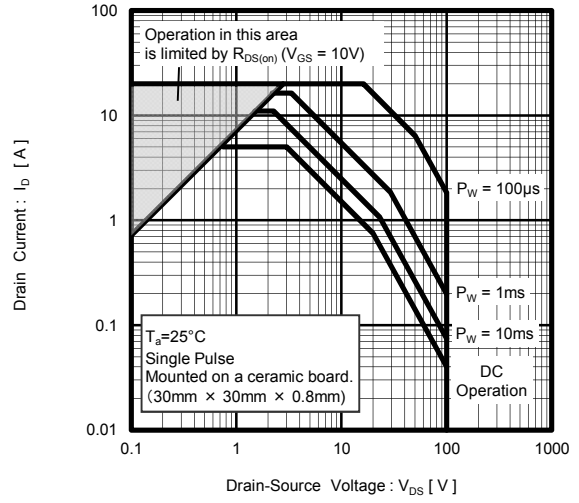
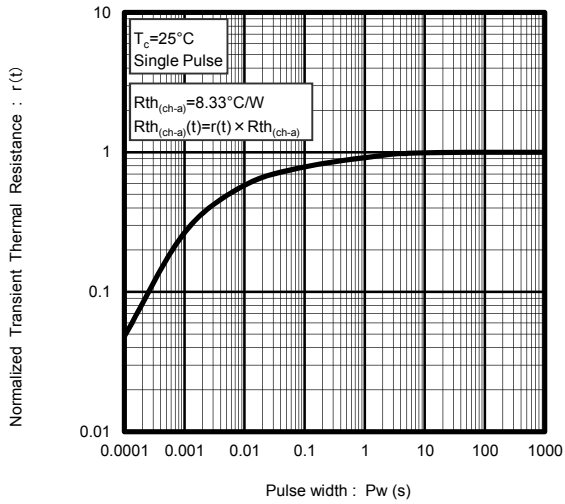


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



●Measurement circuits

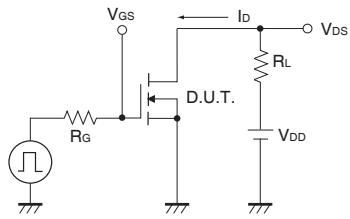


Fig.1-1 Switching time measurement circuit

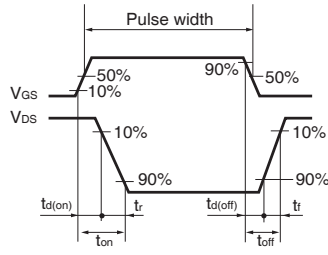


Fig.1-2 Switching waveforms

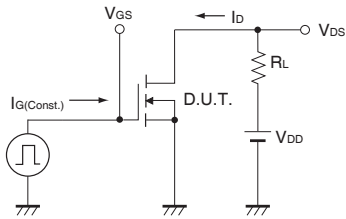


Fig.2-1 Gate charge measurement circuit

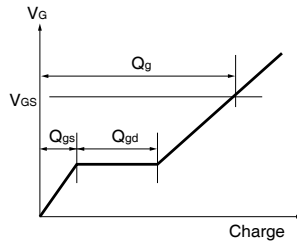


Fig.2-2 Gate Charge Waveform

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